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1. (Amended) A method of imaging a pattern onto a substrate provided with a layer of energy-sensitive material, comprising [the steps of]:

performing a first exposure to image partly said pattern;

performing a second exposure to image partly said pattern,

wherein at least one of said first and second exposures is performed using an illumination mode having a substantially dipolar intensity distribution.

3. (Twice Amended) A method according to claim 1, wherein a first [different] mask is used to define [the] an image formed by [each of] said first [and second exposures] exposure and a second mask is used to define an image formed by said second exposure.

4. (Amended) A method according to claim 3, further comprising [the step of] exchanging masks between said first and second exposures.

5. (Twice Amended) A method according to claim 1, wherein a mask having at least two sub-patterns is used for the first and second exposures, a first of the said

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sub-patterns being used to define [the] an image formed by the first exposure and the second of the sub-patterns being used to define [the] an image formed by the second exposure.

6. (Twice Amended) A method according to claim 1, wherein [the or each dipolar] said illumination mode is used to image linear features of the pattern oriented substantially perpendicular to [the] an axis joining the respective two poles of [the or each dipole mode] said substantially dipolar intensity distribution.

7. (Amended) A method according to claim 6, wherein [the] at least one of a respective mask [or] and a mask sub-pattern is used with [the or each dipolar] said illumination mode exposure and substantially defines only features of the pattern oriented substantially perpendicularly to the axis joining the respective two poles of [the or each dipole mode] said substantially dipolar intensity distribution.

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8. (Twice Amended) A method according to claim 1, wherein [the or each dipolar] said illumination mode has an intensity distribution [comprises] comprising two relatively intense poles and further [comprises one or more] comprising at least one of: a

relatively weak central pole; two relatively weak further poles; and a general relatively weak background intensity.

9. (Twice Amended) A method according to claim 1, further comprising [the step of:] changing at least one of [the] a pole radial position, size and intensity between said first and second exposures.

10. (Twice Amended) A method according to claim 1, wherein said first and second exposures are both performed using dipolar illumination modes and wherein [the] axes of the two dipolar modes are substantially perpendicular to each other.

11. (Twice Amended) A method according to claim 1, wherein [the or each] at least one of the exposures performed using an illumination mode having a substantially dipolar intensity distribution, is performed using polarized electromagnetic radiation.

13. (Amended) A method according to claim 12, wherein the radiation is [thus] polarized [so as] to have an electric field component oriented substantially

B14 perpendicular to [the] an axis joining the respective two poles of the [or each] substantially dipole intensity distribution.

14. (Twice Amended) A method according to claim 1, wherein between the first and second exposures, [the] a focus of [the] a pattern on the substrate is adjusted[, thereby] to ensure that both the first and second exposures are performed at a substantially optimum focus.

15. (Twice Amended) A method according to claim 1, wherein [the or each] at least one of the exposures using an illumination mode having a substantially dipolar intensity distribution[,] is performed using an attenuated phase shift mask.

16. (Amended) A method according to claim 15, wherein [the] an attenuation is [thus] chosen [so as] to balance [the] an energy of radiation of [the] zeroth- and first-order diffracted beams[,] as they are emerging from said pattern and captured by a projection system used to image the patterns on the substrate.

17. (Twice Amended) A device manufacturing method comprising [the steps of]:

providing a substrate which is at least partially covered by a layer of energy-sensitive material;

providing at least one mask for defining a pattern; and

imaging at least part of said mask pattern onto said substrate using a method according to claim 1.

19. (Amended) An apparatus for imaging a pattern onto a substrate provided with a layer of energy sensitive material, said apparatus comprising:

an illumination system [for defining] adapted to illuminate a first mask to define a first illumination mode and to illuminate a second mask to define a second illumination mode [modes];

a projection system [for imaging] adapted to image at least parts of said first and second masks onto [pattern defined by a mask on] said substrate to form at least a portion of said pattern; and

a mask changer [for changing between] constructed and arranged to change positions of said first and second masks with respect to said illumination system;

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wherein at least one of said first and second illumination modes is a dipolar illumination mode and wherein said apparatus is arranged to image said pattern by at least two exposures using respective said first and second illumination modes and mask sub-patterns.

Claim 21, line 2 change "one or more" to --at least one-- and change "elements" to --element--.

Please add the following new claims:

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--22. An apparatus according to claim 20, wherein said illumination system comprises at least one diffractive optical element for defining said first and second illumination modes.

23. A method according to claim 3, wherein said first mask is different from said second mask.--

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wherein at least one of said first and second illumination modes is a dipolar illumination mode and wherein said apparatus is arranged to image said pattern by at least two exposures using respective first and second illumination modes and said first and second masks.

20. (Amended) An apparatus for imaging a pattern onto a substrate provided with a layer of energy sensitive material, said apparatus comprising:

an illumination system [for defining] adapted to illuminate a first mask portion to define a first illumination mode and to illuminate a second mask portion to define a second illumination mode [modes];

a projection system [for imaging] adapted to image at least parts of said first and second mask portions onto [pattern defined by a mask on] said substrate to form at least a portion of said pattern; and

[means for moving the] a mask mover adapted to move a mask containing said first and second mask portions with respect to the projection system, [so as to] said mask mover distinctly positioning [position] first and second mask sub-patterns, located at different positions on the mask, in [the] a radiation beam emerging from the illumination system;

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